

Schottky barrier diode

RB400D

● Applications

High frequency rectification
Switching power supply

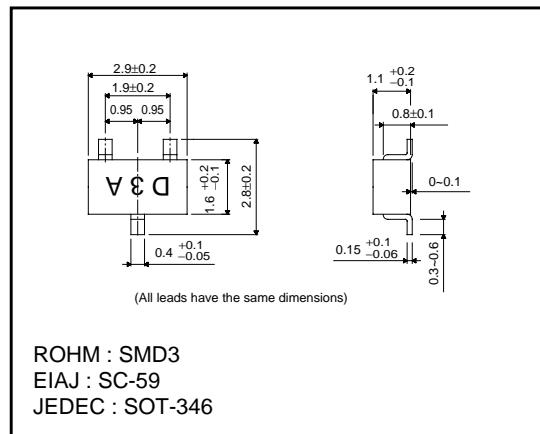
● Features

- 1) Small surface mounting type. (SMD3)
- 2) Low I_R . ($I_R=1\mu A$ Typ.)
- 3) High reliability.

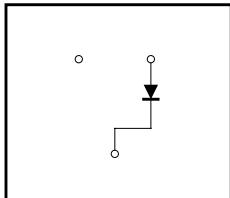
● Construction

Silicon epitaxial planar

● External dimensions (Units : mm)



● Circuit



● Absolute maximum ratings ($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	40	V
Mean rectifying current	I_o	0.5	A
Peak forward surge current	I_{FSM}	3	A
Junction temperature	T_j	125	$^\circ C$
Storage temperature	T_{Stg}	-40~+125	$^\circ C$

● Electrical characteristics ($T_a = 25^\circ C$)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	—	—	0.55	V	$I_F=0.5A$
Reverse current	I_{R1}	—	—	50	μA	$V_R=30V$
	I_{R2}	—	—	30	μA	$V_R=10V$
Capacitance between terminals	C_t	—	125	—	pF	$V_R=0V, f=1MHz$
	C_t	—	20	—	pF	$V_R=10V, f=1MHz$

Note) ESD Sensitive product handling required.

Diodes

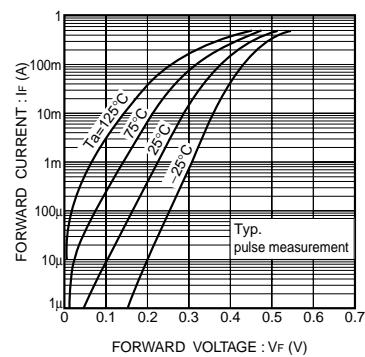
● Electrical characteristic curves ($T_a = 25^\circ\text{C}$)

Fig.1 Forward characteristics

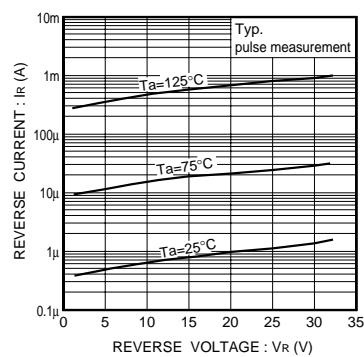


Fig.2 Reverse characteristics

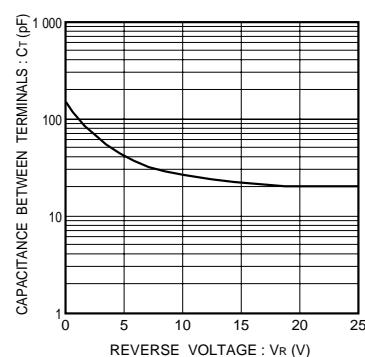


Fig.3 Capacitance between terminals characteristics

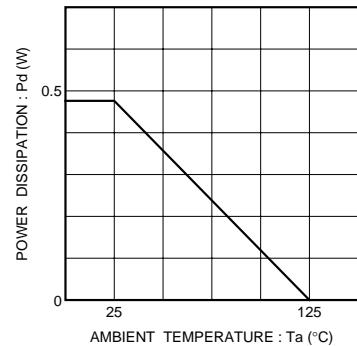


Fig.4 Derating curve